

## GenX3™ 300V IGBTs

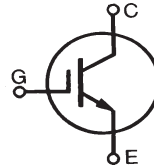
## IXGK400N30A3 IXGX400N30A3

$$V_{CES} = 300V$$

$$I_{C25} = 400A$$

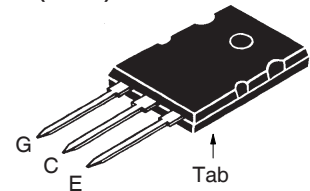
$$V_{CE(sat)} \leq 1.15V$$

Ultra-Low V<sub>sat</sub> PT IGBTs for up to 10kHz Switching

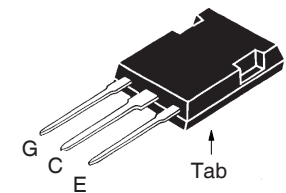


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	300	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	300	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ (Chip Capability)	400	A
$I_{C110}$	$T_C = 110^\circ C$	200	A
$I_{LRMS}$	Terminal Current Limit	160	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	1200	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 400$ @ $0.8 \cdot V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	1000	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
$M_d$	Mounting Torque ( IXGK )	1.13/10	Nm/lb.in.
$F_c$	Mounting Force ( IXGX )	20..120/4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247™ (IXGX)



G = Gate                      E = Emitter  
C = Collector                Tab = Collector

### Features

- Optimized for Low Conduction Losses
- High Avalanche Capability
- International Standard Packages

### Advantages

- High Power Density
- Low Gate Drive Requirement

### Applications

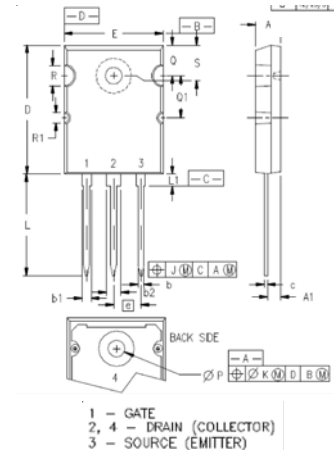
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 1mA$ , $V_{GE} = 0V$	300		V
$V_{GE(th)}$	$I_C = 4mA$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 2 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 400$ nA
$V_{CE(sat)}$	$I_C = 100A$ , $V_{GE} = 15V$ , Note 1 $I_C = 400A$	1.70		1.15 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}$ , $V_{CE} = 10\text{V}$ , Note 1	100	170	S
$C_{ies}$	$V_{CE} = 25\text{V}$ , $V_{GE} = 0\text{V}$ , $f = 1\text{MHz}$		19	nF
$C_{oes}$			1350	pF
$C_{res}$			190	pF
$Q_{g(on)}$	$I_C = 100\text{A}$ , $V_{GE} = 15\text{V}$ , $V_{CE} = 0.5 \cdot V_{CES}$		560	nC
$Q_{ge}$			83	nC
$Q_{gc}$			185	nC
$t_{d(on)}$	<b>Resistive load, <math>T_J = 25^\circ\text{C}</math></b>		45	ns
$t_r$			45	ns
$t_{d(off)}$	$I_C = 100\text{A}$ , $V_{GE} = 15\text{V}$		210	ns
$t_f$		$V_{CE} = 240\text{V}$ , $R_G = 1\Omega$		107
$t_{d(on)}$	<b>Resistive load, <math>T_J = 125^\circ\text{C}</math></b>		47	ns
$t_r$			53	ns
$t_{d(off)}$	$I_C = 100\text{A}$ , $V_{GE} = 15\text{V}$		240	ns
$t_f$		$V_{CE} = 240\text{V}$ , $R_G = 1\Omega$		315
$R_{thJC}$			0.125	$^\circ\text{C/W}$
$R_{thCK}$		0.15		$^\circ\text{C/W}$

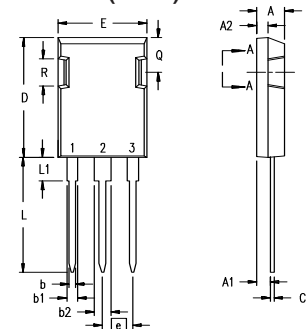
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### TO-264 (IXGK) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.789	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

### PLUS247™ (IXGX) Outline



Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)

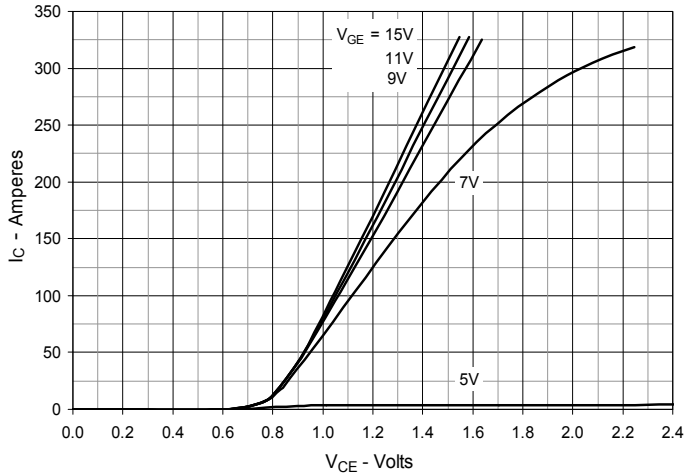
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

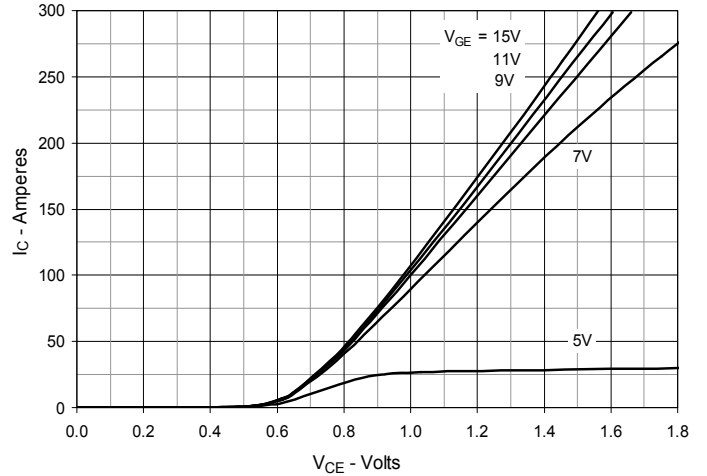
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

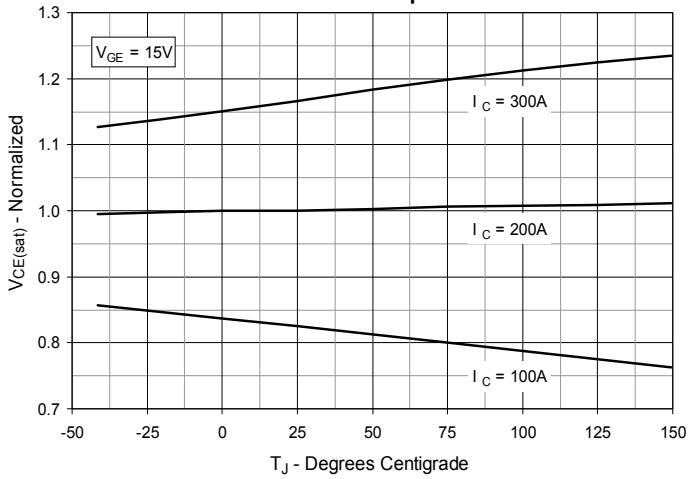
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



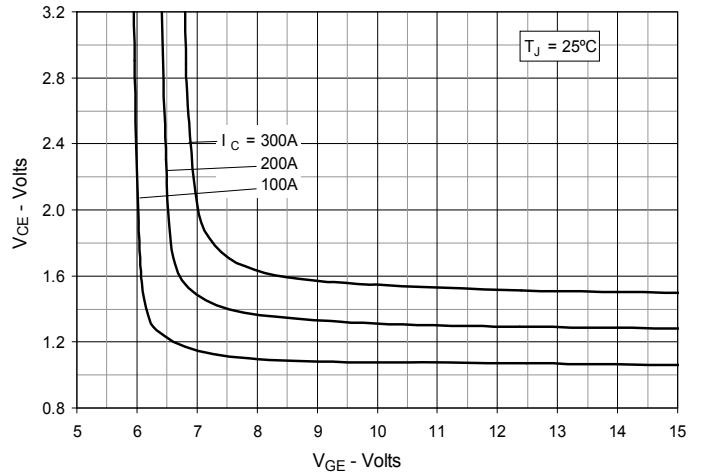
**Fig. 2. Output Characteristics @  $T_J = 125^\circ\text{C}$**



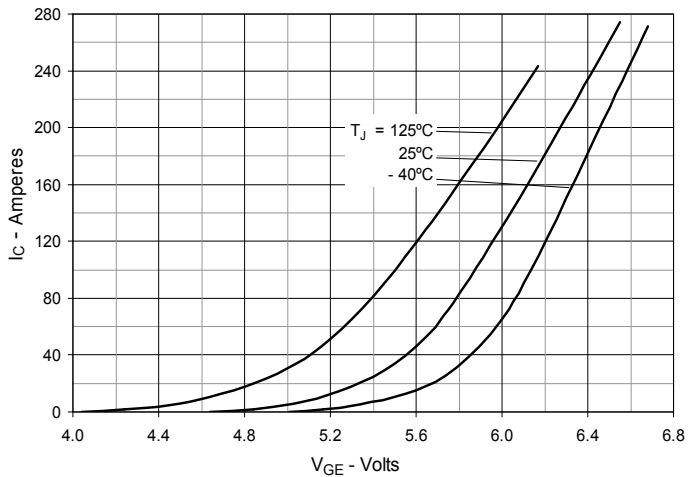
**Fig. 3. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



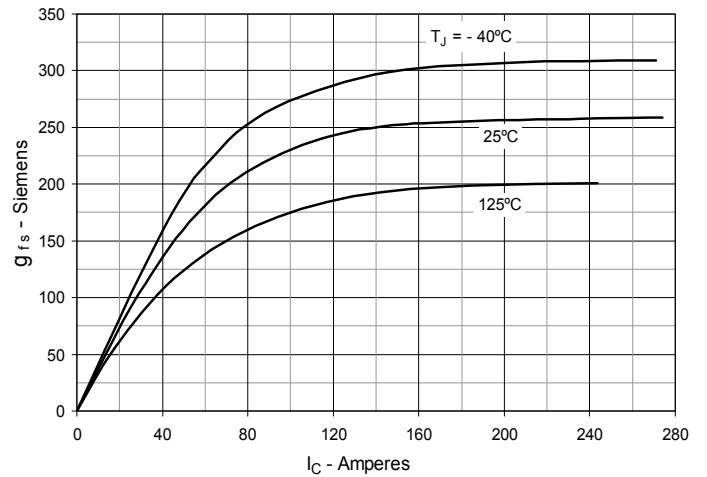
**Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



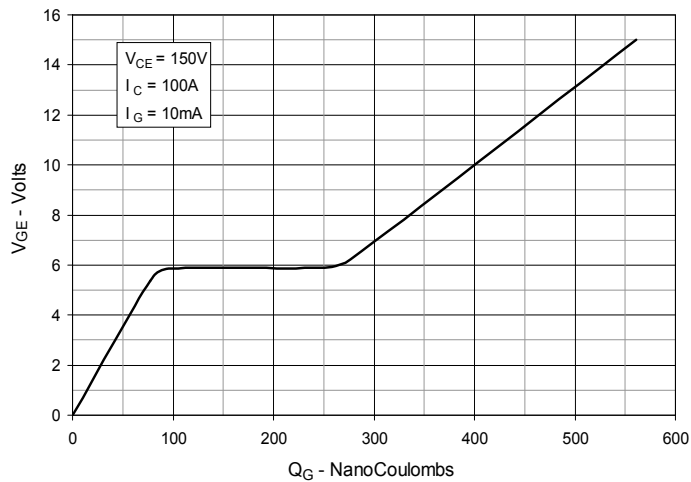
**Fig. 5. Input Admittance**



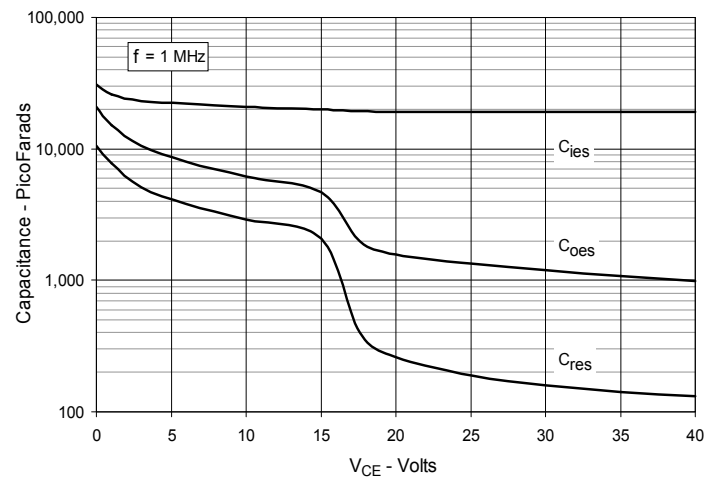
**Fig. 6. Transconductance**



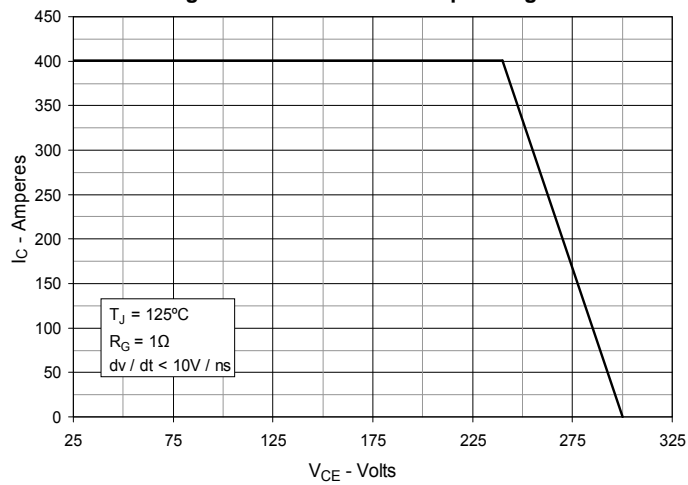
**Fig. 7. Gate Charge**



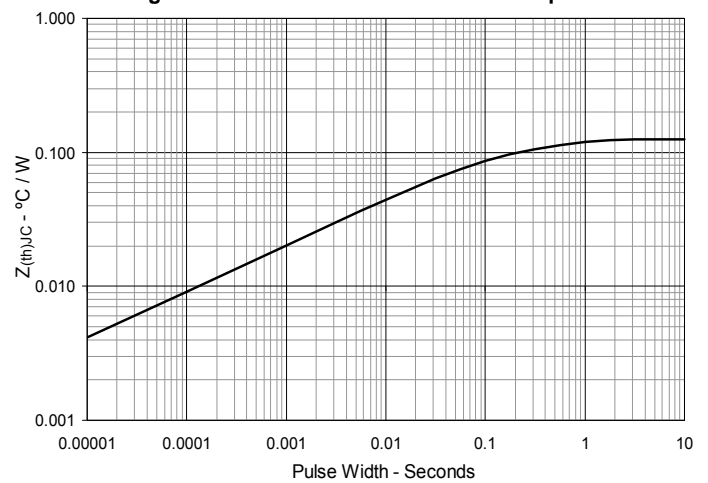
**Fig. 8. Capacitance**



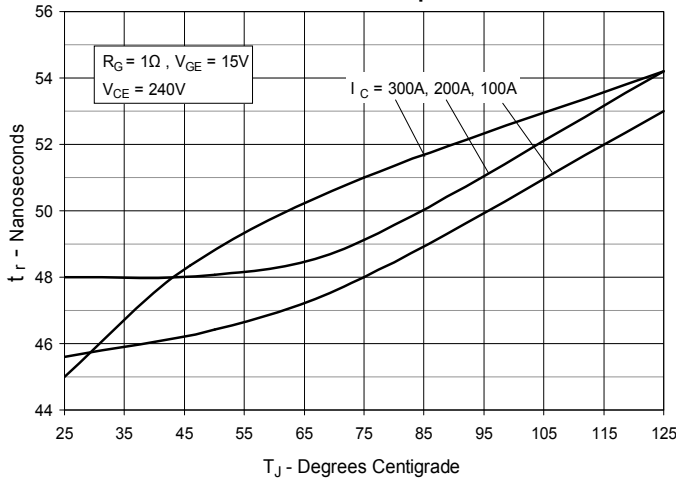
**Fig. 9. Reverse-Bias Safe Operating Area**



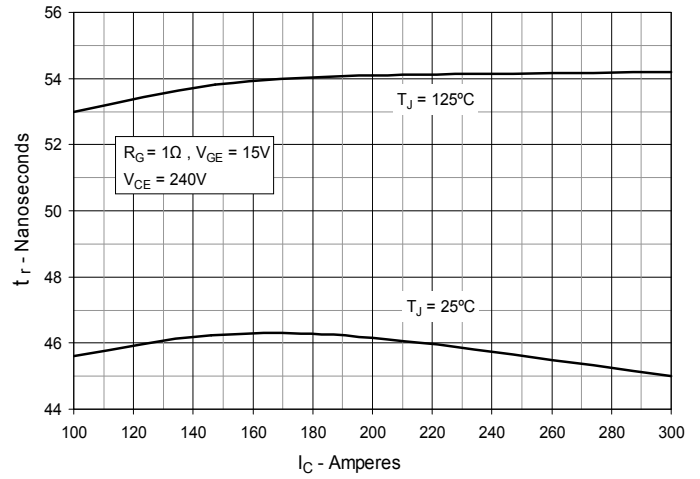
**Fig. 10. Maximum Transient Thermal Impedance**



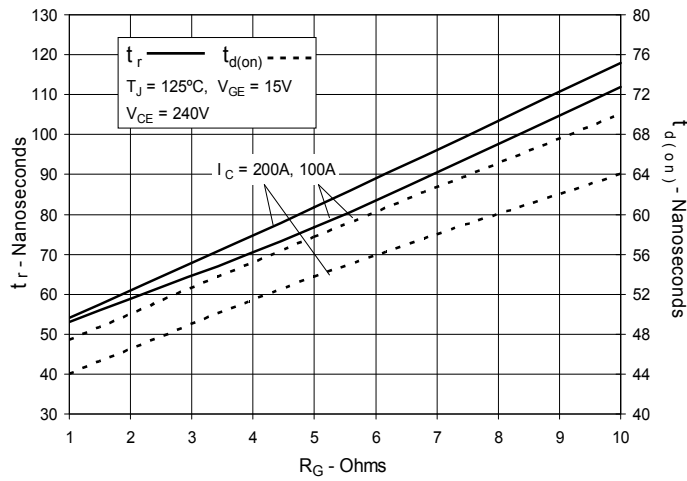
**Fig. 11. Resistive Turn-on Rise Time vs. Junction Temperature**



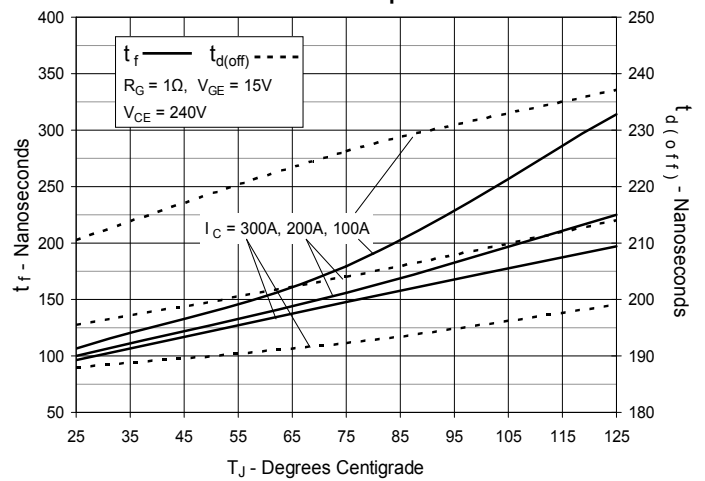
**Fig. 12. Resistive Turn-on Rise Time vs. Collector Current**



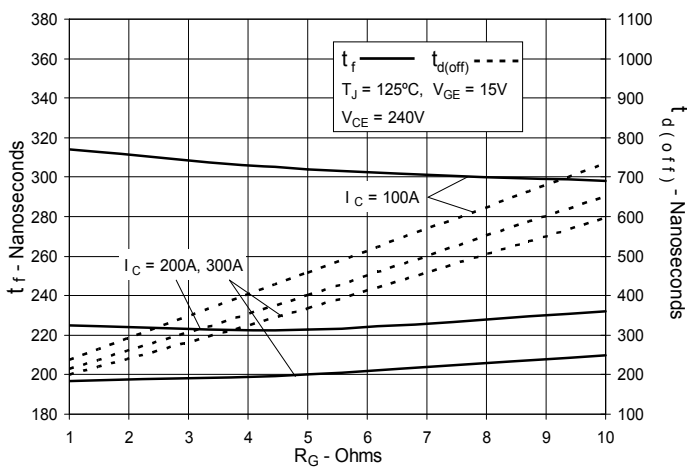
**Fig. 13. Resistive Turn-on Switching Times vs. Gate Resistance**



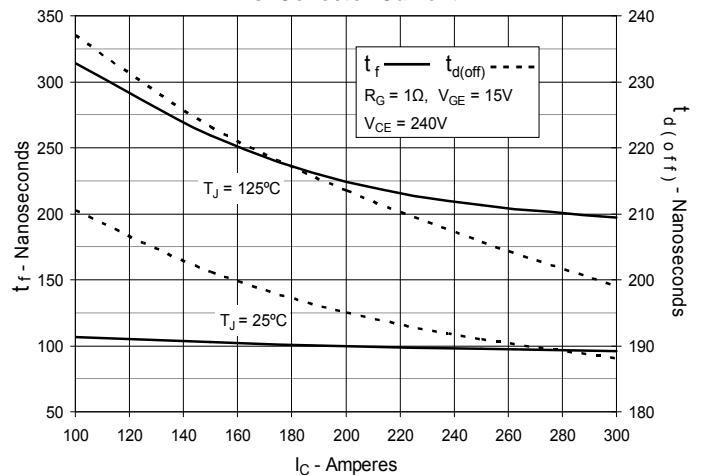
**Fig. 14. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 15. Resistive Turn-off Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Collector Current**



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